TY Semicondutor®

Product specification

RHK003N06

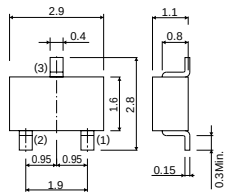
●Structure
TY N-channel MOS FET

●Features
1) Low On-resistance.
2) 4V drive.

●Applications
Switching

●External dimensions (Unit : mm)

SMT3



(1)Source
(2)Gate
(3)Drain

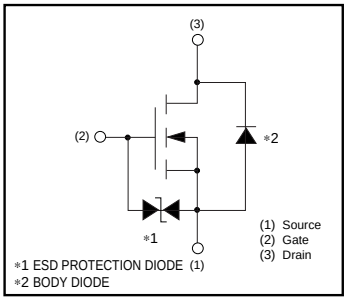
Each lead has same dimensions

Abbreviated symbol : RKS

●Packaging specifications and h_{FE}

Type	Package	Taping
	Code	T146
	Basic ordering unit (pieces)	3000
RHK003N06		○

●Inner circuit



●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	60	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	Continuous	I_D	±300	mA
	Pulsed	I_{DP} *1	±1.2	A
Source current (Body diode)	Continuous	I_S	200	mA
	Pulsed	I_{SP} *1	800	mA
Total power dissipation		P_D *2	200	mW
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	−55 to +150	°C

*1 Pw≤10μs, Duty cycle≤1%
*2 Each terminal mounted on a recommended land

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a) *	625	°C/W

* Each terminal mounted on a recommended land

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●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	±10	μA	V_{GS}=±20V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)\ DSS}$	60	–	–	V	I_D= 1mA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	–	–	1	μA	V_{DS}= 60V, V_{GS}=0V
Gate threshold voltage	$V_{GS\ (th)}$	1.0	–	2.5	V	V_{DS}= 10V, I_D= 1mA
Static drain-source on-state resistance	$R_{DS\ (on)}$*	–	0.7	1.0	Ω	I_D= 300mA, V_{GS}= 10V
		–	1.1	1.5	Ω	I_D= 300mA, V_{GS}= 4V
Forward transfer admittance	$\|Y_{fs}\|$ *	0.2	–	–	S	V_{DS}= 10V, I_D= 300mA
Input capacitance	C_{iss}	–	33	–	pF	V_{DS}= 10V
Output capacitance	C_{oss}	–	14	–	pF	V_{GS}=0V
Reverse transfer capacitance	C_{rss}	–	9	–	pF	f=1MHz
Turn-on delay time	$t_{d\ (on)}$ *	–	6	–	ns	V_{DD}≒ 30V
Rise time	t_r *	–	5	–	ns	I_D= 150mA
Turn-off delay time	$t_{d\ (off)}$ *	–	13	–	ns	V_{GS}= 10V R_L=200Ω
Fall time	t_f *	–	80	–	ns	R_G=10Ω
Total gate charge	Q_g *	–	3	6	nC	V_{DD}≒30V
Gate-source charge	Q_{gs} *	–	0.6	–	nC	V_{GS}= 10V
Gate-drain charge	Q_{gd} *	–	0.5	–	nC	I_D= 300mA

*Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD}*	–	–	1.2	V	I_S= 300mA, V_{GS}=0V

*Pulsed